

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A stacked piezoelectric device comprising piezoelectric layers composed of a piezoelectric material and internal electrode layers containing Cu, each of the piezoelectric layers being stacked alternately with each of the internal electrode layers, wherein the internal electrode layer contains not less than 50 percent by weight of Cu element, and wherein, between the internal electrode layer and the piezoelectric layer, there is a diffusion region formed by mutual diffusion of components of the internal electrode layer and the piezoelectric layer to the other layer and comprising at least one component of the piezoelectric material and Cu,

wherein the diffusion region occupies not less than 90 percent of an area of the whole interface between the internal electrode layer and the piezoelectric layer, and a thickness of the diffusion region is not more than 10 percent of a thickness of the internal electrode layer.

2. (Original) A stacked piezoelectric device according to claim 1, wherein the internal electrode layer contains not less than 95.0 percent by weight of Cu element.

3. (Original) A stacked piezoelectric device according to claim 1, wherein the internal electrode layer contains not less than 99.0 percent by weight of Cu element.

4. (Original) A stacked piezoelectric device according to claim 1, wherein the internal electrode layer is composed of a pure copper metal containing not less than 99.0 percent by weight of Cu element.

5. (Original) A stacked piezoelectric device according to claim 1, wherein the internal electrode layer is composed of a copper alloy containing not less than 95.0 percent by weight of Cu element.

Claim 6. (Canceled).

7. (Original) A stacked piezoelectric device according to claim 1, wherein the diffusion region is a region having a Cu concentration of 1 percent to 0.95A percent by weight, wherein A represents Cu element content in percent by weight in the internal electrode layer.

8. (Original) A stacked piezoelectric device according to claim 1, wherein a thickness of the diffusion region is from 0.001 to 1 micrometer.

9. (Original) A stacked piezoelectric device according to claim 1, wherein the diffusion region exists continuously in both sides of an interface of the internal electrode layer and the piezoelectric layer, and the interface is located in the diffusion region, and wherein a part, closer to the internal electrode layer than the interface, of the diffusion region has an oxygen (O) content of not more than 10 percent by weight.

10. (Original) A stacked piezoelectric device according to claim 1, wherein the piezoelectric material constituting the piezoelectric layer comprises PZT which is a $\text{Pb}(\text{Zr,Ti})\text{O}_3$ -based oxide having a perovskite structure, and Pb, Cu, and O elements coexist in the diffusion region.

11. (Original) A stacked piezoelectric device according to claim 1, which is a piezoelectric actuator for an injector used as a driving source of an injector.

Claims 12-19. (Canceled).